



Features

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TSM80N08 75V N-Channel Power MOSFET

TO-220

Advanced Trench Technology

Low Crss typical @ 203pF (Typ.)

Note: "G" denotes for Halogen Free

Low gate charge typical @ 91.5nC (Typ.)

Low $R_{DS(ON)} 8m\Omega$ (Max.)

Ordering Information

Part No.

TSM80N08CZ C0G

- Pin Definition:
- 1. Gate
- 2. Drain 3. Source

PRODUCT SUMMARY

V	os (V)	R _{DS(on)} (mΩ)	I _D (A)
	75	8 @ V _{GS} =10V	80

Block Diagram

Gate O

N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Package

TO-220

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	75	V	
Gate-Source Voltage		V _{GS}	±25	V	
	T _C =25°C		80	A	
Continuous Drain Current	T _C =70°C	– I _D	60		
Continuous Drain Current	T _A =25°C		12		
	T _A =70°C		9		
Drain Current-Pulsed Note 1		I _{DM}	320	А	
Avalanche Current, L=0.3mH		I _{AS}	35	А	
Avalanche Energy, L=0.3mH		E _{AS}	183	mJ	
	T _C =25°C		113.6	w	
Maximum Bawar Dissinction	T _C =70°C		72.7		
Maximum Power Dissipation	T _A =25°C	– P _D	2		
	T _A =70°C		1.3		
Storage Temperature Range		T _{STG}	-55 to +150	°C	
Operating Junction Temperature Range		TJ	-55 to +150	°C	

Packing

50pcs / Tube

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	RƏ _{JC}	1.1	°C/W
Thermal Resistance - Junction to Ambient	RƏ _{JA}	62.5	°C/W

Notes: Surface mounted on FR4 board t \leq 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250uA$	BV _{DSS}	75			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 40A$	R _{DS(ON)}		6	8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \text{uA}$	V _{GS(TH)}	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge		Qg		91.5		
Gate-Source Charge	$V_{DS} = 30V, I_D = 40A,$	Q _{gs}		34		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}		19.9		
Input Capacitance		C _{iss}		3905		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		371		pF
Reverse Transfer Capacitance		C _{rss}		203		
Switching						
Turn-On Delay Time		t _{d(on)}		21.5		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t _r		11		
Turn-Off Delay Time	$ID = 1A, R_G = 3.3\Omega$	t _{d(off)}		73		nS
Turn-Off Fall Time		t _f		66		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =20A	V _{SD}	-	0.8	1.3	V
Reverse Recovery Time	I _S = 40A, T _J =25 °C	t _{fr}		36		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q _{fr}		45		nC

Notes:

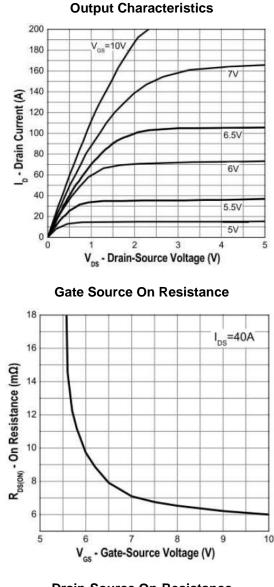
Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
Rθ_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rθ_{JC} is guaranteed by design while Rθ_{CA} is determined by the user's board design. Rθ_{JA} shown below for single device operation on FR-4 in still air



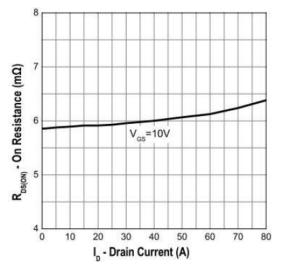
COMPLIANCE

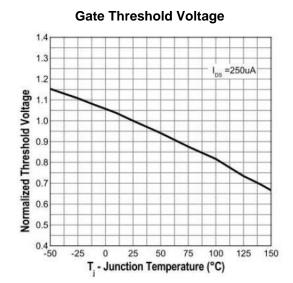
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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

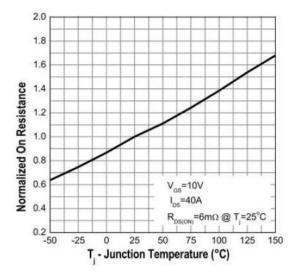


Drain-Source On-Resistance

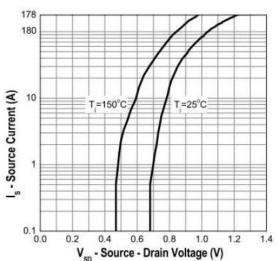




Drain-Source On Resistance



Source-Drain Diode Forward Voltage

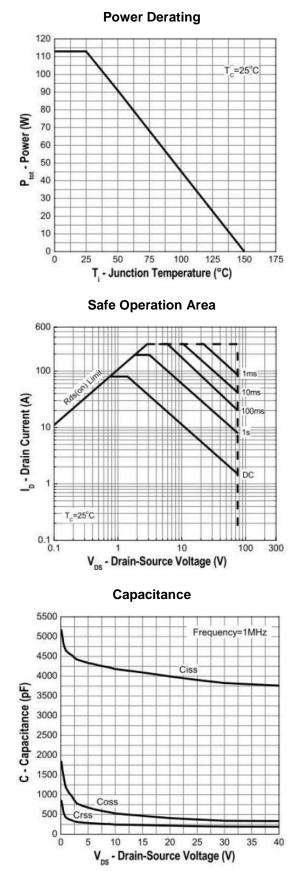


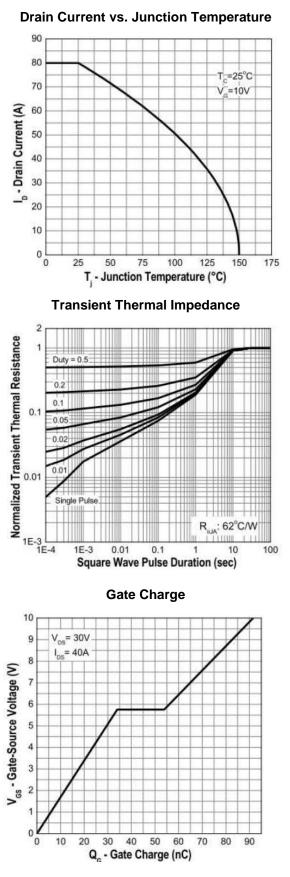
5 TAIWAN SEMICONDUCTOR

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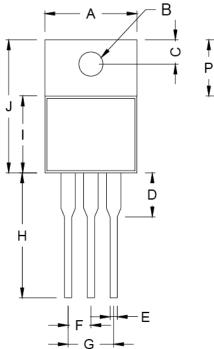


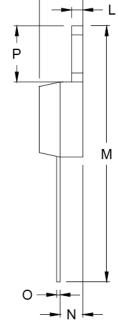




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TO-220 Mechanical Drawing





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TO-220 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	10.000	10.500	0.394	0.413	
В	3.740	3.910	0.147	0.154	
С	2.440	2.940	0.096	0.116	
D	-	6.350	-	0.250	
Е	0.381	1.106	0.015	0.040	
F	2.345	2.715	0.092	0.058	
G	4.690	5.430	0.092	0.107	
Н	12.700	14.732	0.500	0.581	
J	14.224	16.510	0.560	0.650	
К	3.556	4.826	0.140	0.190	
L	0.508	1.397	0.020	0.055	
М	27.700	29.620	1.060	1.230	
Ν	2.032	2.921	0.080	0.115	
0	0.255	0.610	0.010	0.024	
Р	5.842	6.858	0.230	0.270	



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